

IN THE CLAIMS

Please amend the claims as follows:

1-23. (Cancel)

24. (Currently Amended) A substrate processing apparatus, comprising:

a development and cleaning portion developing a photo sensitive material on the substrate with a developing solution and cleaning the developing solution with a cleaning solution; and

a radiating portion radiating an electron beam ~~a beam with a wavelength shorter than that of a visible ray~~ on the photo sensitive material before the photo sensitive material and the cleaning solution are dried out.

25. (Cancel)

26. (Cancel)

27. (Original) The apparatus as set forth in claim 24,

wherein the radiating portion is capable of forming a hermetic zone capable of reducing a pressure.

28. (Original) The apparatus as set forth in claim 27, further comprising:

a gas supplying mechanism supplying an inert gas to the hermetic zone.

29. (Original) The apparatus as set forth in claim 24, further comprising:

a supplying mechanism supplying a surface-active agent on the substrate.

30. (New) The apparatus as set forth in claim 24, further comprising:

a first chamber;

a second chamber; and

wherein the development and cleaning portion is disposed in the first chamber and the

radiating portion is disposed in the second chamber different from the first chamber.

31. (New) The apparatus as set forth in claim 24, further comprising:

a selecting portion selecting the depth of radiation of the electron beam.

32. (New) A substrate processing apparatus, comprising:

a development and cleaning portion developing a photo sensitive material on the substrate with a developing solution and cleaning the developing solution with a cleaning solution; and

a radiating portion, capable of forming a hermetic zone capable of reducing a pressure, radiating a beam with a wavelength shorter than that of a visible ray on the photo sensitive material before the photo sensitive material and the cleaning solution are dried out.

33. (New) The apparatus as set forth in claim 32,

wherein the beam is an ultraviolet ray.

34. (New) The apparatus as set forth in claim 32, further comprising:

a gas supplying mechanism supplying an inert gas to the hermetic zone.

35. (New) The apparatus as set forth in claim 32, further comprising:

a supplying mechanism supplying a surface-active agent on the substrate.

36. (New) The apparatus as set forth in claim 32,

a first chamber;

a second chamber; and

wherein the development and cleaning portion is disposed in the first chamber and the radiating portion is disposed in the second chamber different from the first chamber.

37. (New) The apparatus as set forth in claim 32, further comprising:

a selecting portion selecting the depth of radiation of the radiated beam.